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Infineon Technologies SIDC56D170E6

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Distributor of Infineon Technologies: Excellent Integrated System Limited

Datasheet of SIDC56D170E6 - DIODE GEN PURP 1.7KV 75A WAFER

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



SIDC56D170E6

Fast switching diode chip in Emitter Controlled -Technology

Features:

- 1700V technology, Emitter Controlled
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

 power modules and discrete devices



Applications:

SMPS, resonant applications, drives

Chip Type	V _R	I F	Die Size	Package
SIDC56 D170E6	1700V	75A	7.5 x 7.5mm ²	sawn on foil

Mechanical Parameter				
Raster size	7.5 x 7.5			
Area total	56.25	mm ²		
Anode pad size	5.48 x 5.48			
Thickness	200	μm		
Wafer size	150	mm		
Max. possible chips per wafer	247			
Passivation frontside	Photoimide			
Pad metal	3200 nm AlSiCu			
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding			
Die bond Electrically conductive glue or solder				
Wire bond	AI, ≤500μm			
teject ink dot size Ø 0.65mm; max 1.2mm				
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C			

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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit	
Repetitive peak reverse voltage	V_{RRM}	T _{vj} = 25 °C	1700	V	
Continuous forward current	I _F	<i>T</i> _{vj} < 150°C	1)	A	
Maximum repetitive forward current	I _{FRM}	<i>T</i> _{vj} < 150°C	150	7 ^	
Junction temperature range	T _{vj}		-40+175	°C	
Operating junction temperature	$T_{\rm vj}$		-40+150	°C	
Dynamic ruggedness ²⁾	P _{max}	$I_{\text{Fmax}} = 150\text{A}, \ V_{\text{Rmax}} = 1700\text{V}$ $T_{\text{vj}} \le 150^{\circ}\text{C}$	tbd	kW	

¹⁾ depending on thermal properties of assembly

Static Characteristic (tested on wafer), $T_{vj} = 25$ °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	Joint
Reverse leakage current	I _R	V _R =1700V			27	μA
Cathode -Anode breakdown Voltage	V_{BR}	I _R =5m A	1700			V
Diode forward voltage	V _F	I _F =75 A		2.15		V

Further Electrical Characteristic

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

²⁾ not subject to production test - verified by design/characterisation

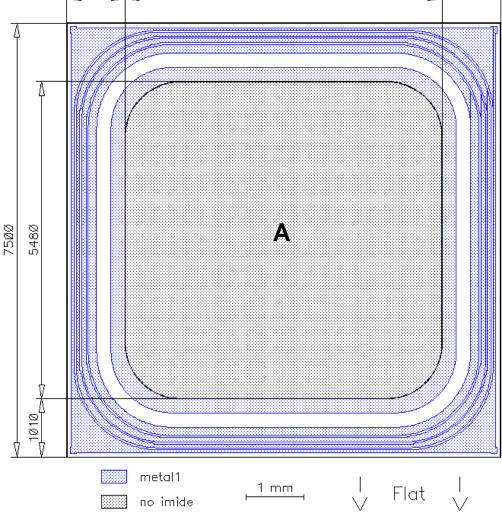




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Chip Drawing





A: Anode pad

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Description

AQL 0.65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

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